

AMENDMENT TO THE SPECIFICATION:

Please amend the paragraph beginning on page 10, line 6.

--The second nitride based semiconductor layer may be formed so as to cover a region above the opening and a region on the current blocking layer. The semiconductor laser device may further comprise an [[type]] electrode formed on the second nitride based semiconductor layer.--

Please amend the paragraph beginning on page 15, line 17.

The step of forming the second nitride based semiconductor layer may comprise the step of forming the second nitride based semiconductor layer for covering a region above the opening and a region on the current blocking layer. Further, it may further comprise the step of forming an [[type]] electrode on the second nitride based semiconductor layer.